

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1.-30. (Canceled)

31. (Currently Amended) A semiconductor device comprising:

a first substrate;

a thin film transistor over said first substrate;

a second substrate opposing to said first substrate;

a wiring provided with said second substrate;

a connecting wiring for electrically connecting said wiring of the second substrate to said thin film transistor over said first substrate, wherein said connecting wiring comprises a metallic film over said first substrate and a transparent conductive film over said metallic film;

an insulating film over said first substrate; and

an anisotropic conductive film over said insulating film and said connecting wiring,

wherein said metallic film has a taper shape,

wherein the wiring of the second substrate is connected to a portion of the connecting wiring, and

wherein ~~both side surfaces~~ a side surface of the ~~portion of the connecting wiring~~  
metallic film and a side surface of the transparent conductive film are in contact with the insulating film.

32. (Previously Presented) A semiconductor device according to claim 31 wherein the insulating film comprises a same material as that contained in an insulating film between a gate wiring and a source wiring of the thin film transistor.

33.-34. (Canceled)

35. (Previously Presented) A semiconductor device according to claim 31 wherein a thickness of the metallic film is between 100 nm and 1  $\mu$ m.

36. (Previously Presented) A semiconductor device according to claim 31 wherein the metallic film comprises Al.

37. (Previously Presented) A semiconductor device according to claim 31 wherein the metallic film comprises W.

38. (Previously Presented) A semiconductor device according to claim 31 wherein the metallic film is a lamination film comprising a W layer and a layer comprising W and N.

39. (Previously Presented) A semiconductor device according to claim 31 wherein a thickness of the transparent conductive film is between 50 nm and 0.5  $\mu$ m.

40. (Previously Presented) A semiconductor device according to claim 31 wherein the transparent conductive film comprises zinc oxide.

41. (Previously Presented) A semiconductor device according to claim 31 wherein the transparent conductive film comprises zinc oxide and indium oxide.

42. (Previously Presented) The semiconductor device according to claim 31 wherein said semiconductor device is one of a liquid crystal display device and EL display device.

43. (Currently Amended) A semiconductor device comprising:

a first substrate;

a thin film transistor over said first substrate;

a second substrate opposing to said first substrate;

a wiring provided with said second substrate;

a connecting wiring for electrically connecting said wiring of the second substrate to said thin film transistor over said first substrate, wherein said connecting wiring comprises a metallic film over said first substrate and a transparent conductive film over said metallic film;

a column-shape spacer formed over said thin film transistor for maintaining a space between said first substrate and said second substrate;

an insulating film over said first substrate; and

an anisotropic conductive film over said insulating film and said connecting wiring, wherein said metallic film has a taper shape,

wherein the wiring of the second substrate is connected to a portion of the connecting wiring, and

wherein ~~both side surfaces~~ a side surface of the ~~portion of the connecting wiring~~ metallic film and a side surface of the transparent conductive film are in contact with the insulating film.

44.-45. (Canceled)

46. (Previously Presented) A semiconductor device according to claim 43 wherein a thickness of the metallic film is between 100 nm and 1  $\mu$ m.

47. (Previously Presented) A semiconductor device according to claim 43 wherein the metallic film comprises Al.

48. (Previously Presented) A semiconductor device according to claim 43 wherein the metallic film comprises W.

49. (Previously Presented) A semiconductor device according to claim 43 wherein the metallic film is a lamination film comprising a W layer and a layer comprising W and N.

50. (Previously Presented) A semiconductor device according to claim 43 wherein a thickness of the transparent conductive film is between 50 nm and 0.5  $\mu\text{m}$ .

51. (Previously Presented) A semiconductor device according to claim 43 wherein the transparent conductive film comprises zinc oxide.

52. (Previously Presented) A semiconductor device according to claim 43 wherein the transparent conductive film comprises zinc oxide and indium oxide.

53. (Previously Presented) The semiconductor device according to claim 43 wherein said semiconductor device is one of a liquid crystal display device and EL display device.

54. (Canceled)

55. (Previously Presented) A semiconductor device according to claim 31 wherein the connecting wiring is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.

56. (Previously Presented) A semiconductor device according to claim 43 wherein the connecting wiring is formed of the same materials as those of a source wiring and a drain wiring of the thin film transistor.

57.-58. (Canceled)

59. (Previously Presented) The semiconductor device according to claim 31, wherein the anisotropic conductive film covers the portion of the connecting wiring.

60. (Previously Presented) The semiconductor device according to claim 31, wherein the thin film transistor is selected from the group consisting of a top gate thin film transistor and a bottom gate thin film transistor.

61. (Previously Presented) The semiconductor device according to claim 31, wherein the anisotropic conductive film comprises a conductive grain dispersed to an adhesive.

62. (Previously Presented) The semiconductor device according to claim 31, wherein the anisotropic conductive film is not in contact with the both side surfaces of the portion of the connecting wiring.

63. (Previously Presented) The semiconductor device according to claim 31, wherein the thin film transistor is formed in a driver circuit.

64. (Canceled)

65. (Previously Presented) The semiconductor device according to claim 43, wherein the anisotropic conductive film covers the portion of the connecting wiring.

66. (Previously Presented) The semiconductor device according to claim 43, wherein the thin film transistor is selected from the group consisting of a top gate thin film transistor and a bottom gate thin film transistor.

67. (Previously Presented) The semiconductor device according to claim 43, wherein the anisotropic conductive film comprises a conductive grain dispersed to an adhesive.

68. (Previously Presented) The semiconductor device according to claim 43, wherein the anisotropic conductive film is not in contact with the both side surfaces of the portion of the connecting wiring.

69. (Previously Presented) The semiconductor device according to claim 43, wherein the thin film transistor is formed in a driver circuit.

70. (Canceled)